

N-Channel Enhancement Mode Power MOSFET

Description

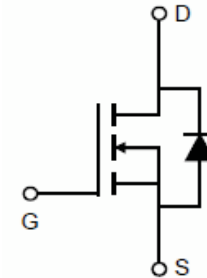
The RM50N60DF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

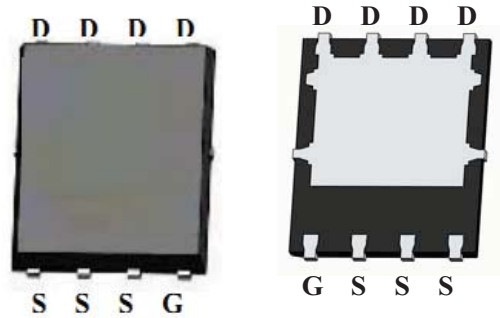
- $V_{DS} = 60V, I_D = 50A$
 $R_{DS(ON)} < 16m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 18m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- PWM
- Load Switching
- P/N suffix V means AEC-Q101 qualified, e.g:RM50N60DFV
- Halogen-free



Schematic Diagram



Top View

Bottom View

100% UIS TESTED!
100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
50N60	RM50N60DF	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	50	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	33	A
Pulsed Drain Current	I_{DM}	120	A
Maximum Power Dissipation	P_D	104	W
Derating factor		0.6	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	390	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.2	$^\circ C/W$
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Electrical Characteristics (T_C=25°C unless otherwise noted)

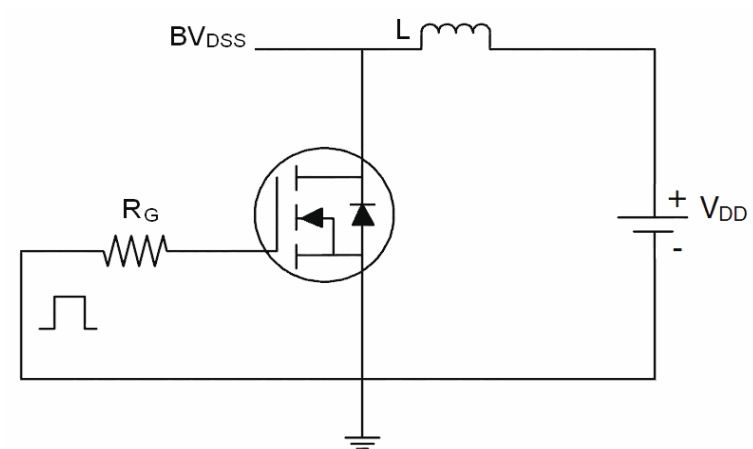
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	10	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	-	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =25A	-	14	16	mΩ
		V _{GS} =4.5V, I _D =15A	-	-	18	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =30A	-	71	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{ISS}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	1920	2300	pF
Output Capacitance	C _{OSS}		-	185	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	80	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =30V, I _D =20A, V _{GS} =10V, R _G =3.3Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	43	-	nS
Turn-Off Delay Time	t _{d(off)}		-	47	-	nS
Turn-Off Fall Time	t _f		-	80	-	nS
Total Gate Charge	Q _g	V _{DS} =48V, I _D =20A, V _{GS} =4.5V	-	33	45	nC
Gate-Source Charge	Q _{gs}		-	5	-	nC
Gate-Drain Charge	Q _{gd}		-	21	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.3	V
Diode Forward Current (Note 2)	I _S		-	-	80	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _S = 10A	-	30	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note 3)	-	18	-	nC

Notes:

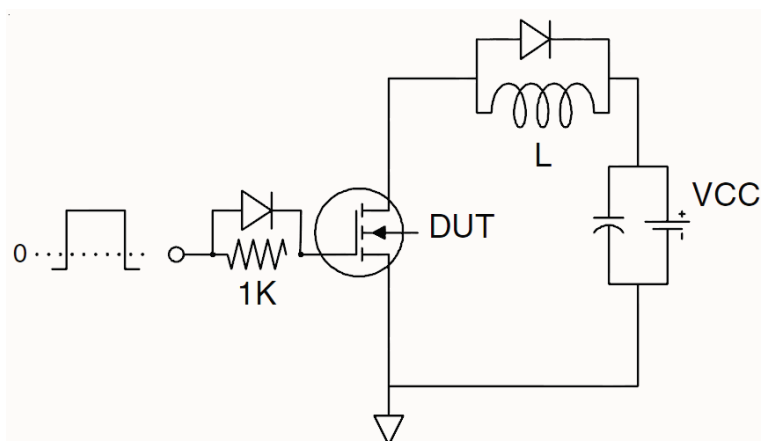
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω

Test circuit

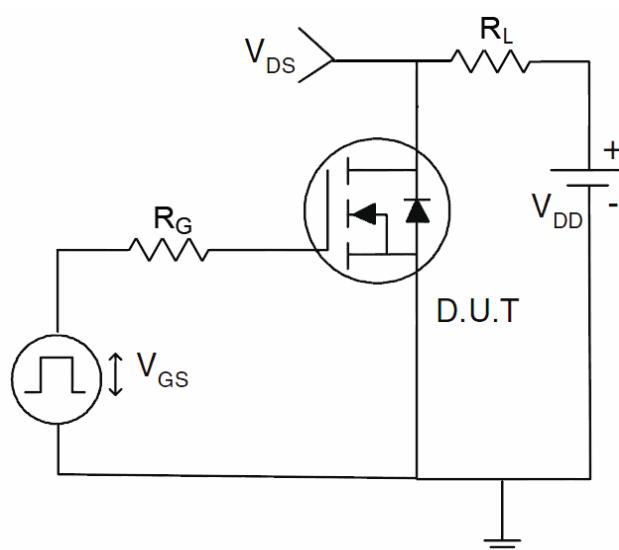
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM50N60DF)

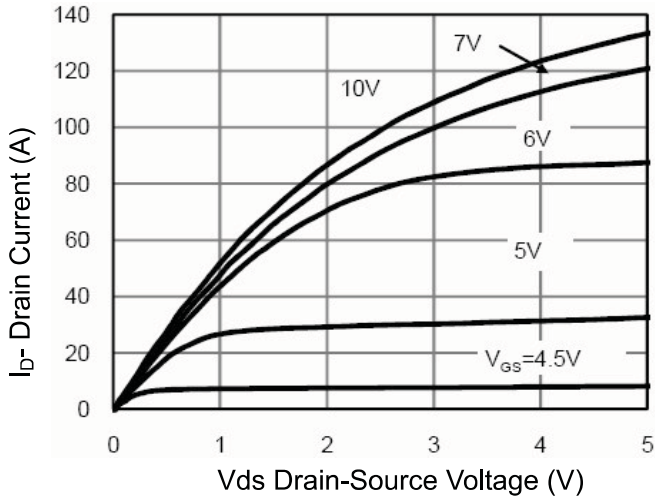


Figure 1 Output Characteristics

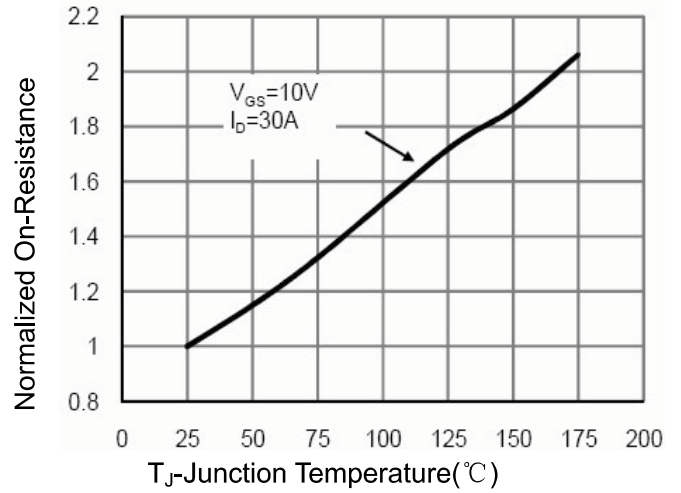


Figure 4 R_{dson} -Junction Temperature

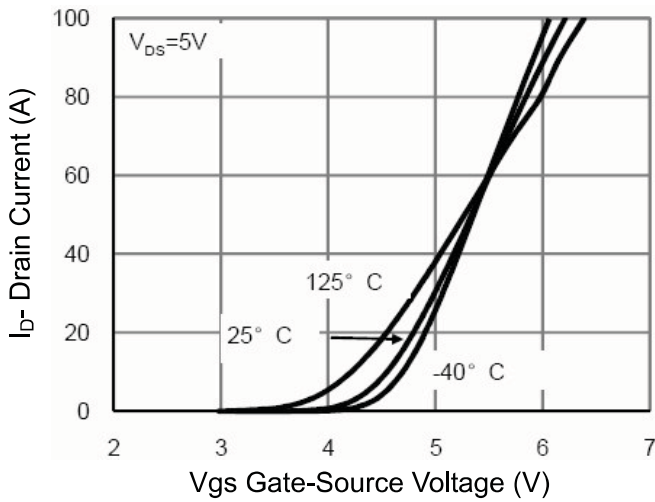


Figure 2 Transfer Characteristics

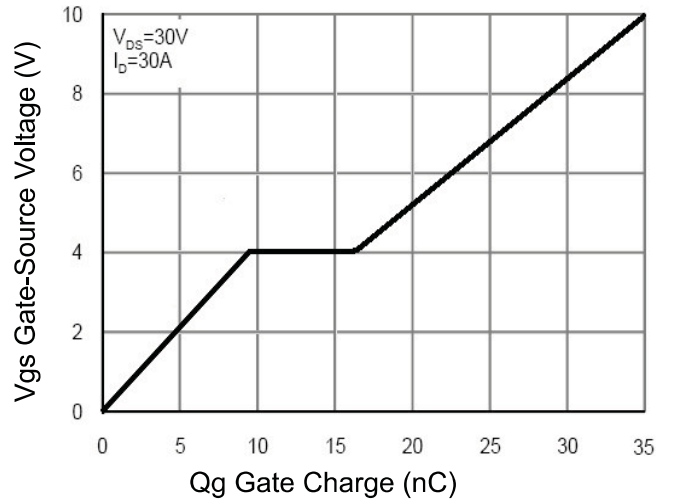


Figure 5 Gate Charge

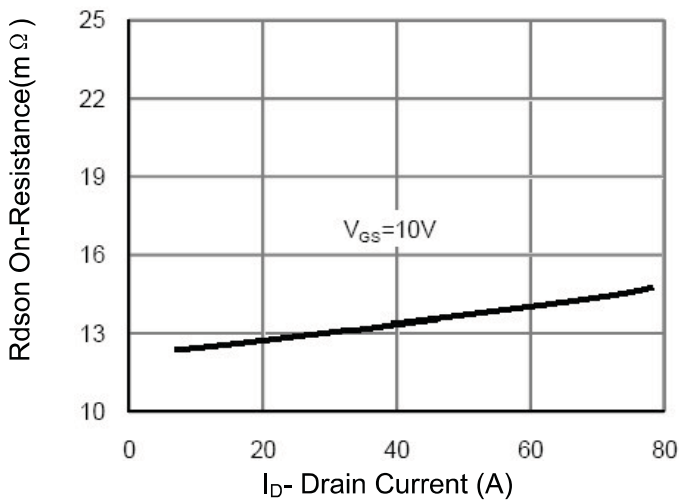


Figure 3 R_{dson} - Drain Current

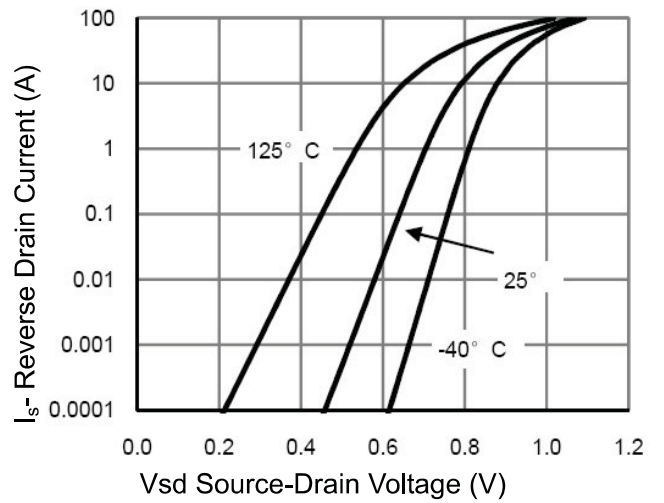


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM50N60DF)

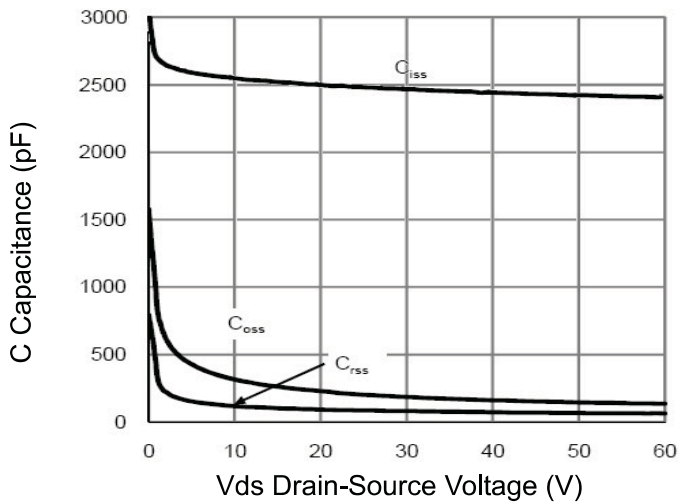


Figure 7 Capacitance vs Vds

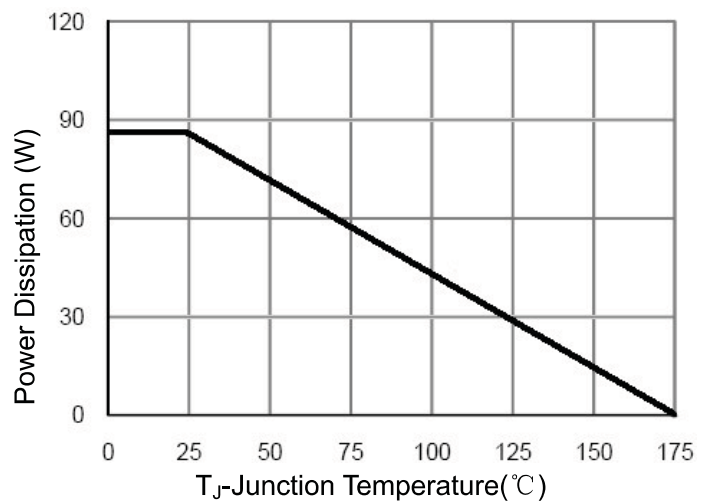


Figure 9 Power De-rating

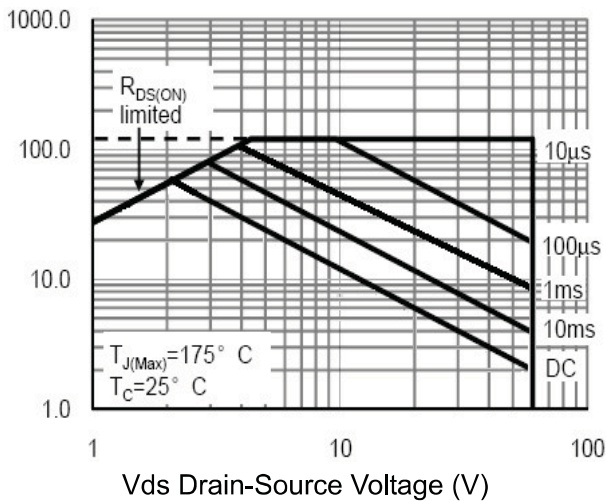


Figure 8 Safe Operation Area

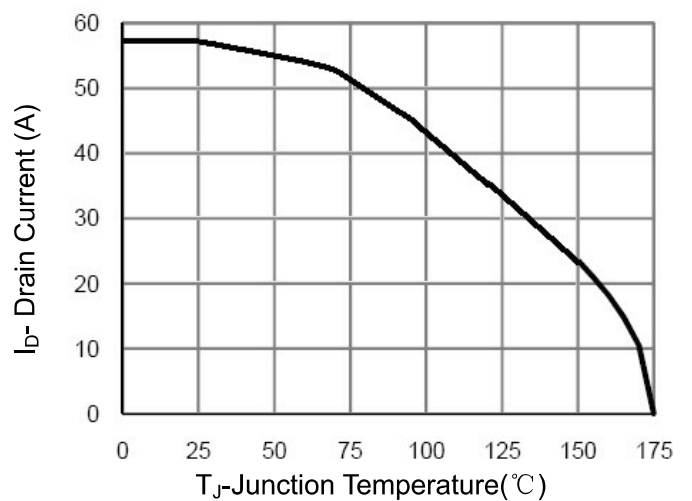


Figure 10 I_D Current- Junction Temperature

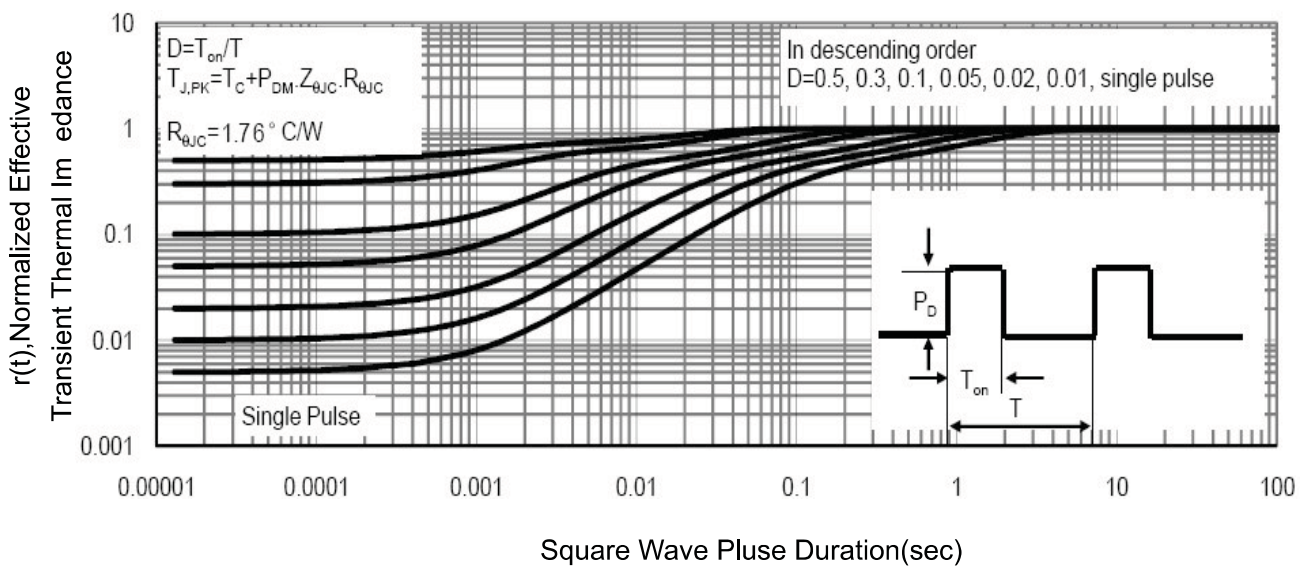
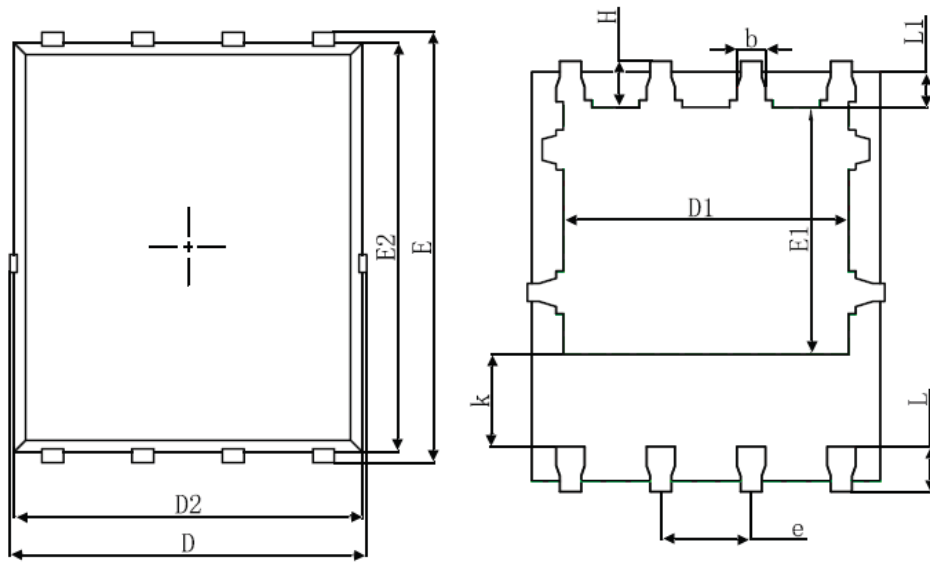


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



Top View
[顶视图]

Bottom View
[背视图]

Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	8°	12°	8°	12°

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